

UR Series for GaN in Multiple Types of 150/200 mm Production Reactors



UR26K-CCD

- Large scale deposition system
- Turn key solution due to integrated cassette-to-cassette cleaning module

World's First Fully Automated MOCVD Platform

Lowest Achievable Cost of Ownership with High Throughput Reactor and Integrated Dry Cleaning Technology



Integration of dry cleaning system



Cassette-to-Cassette System

Fully automated cassette-to-cassette (CtoC) wafer loading increases throughput, reduces contamination from wafer handling, and increases overall product yield

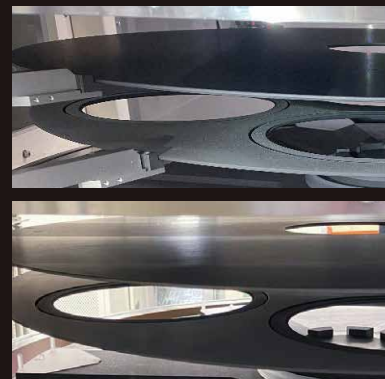
Integrated Dry Cleaning System

Maximizes the productivity of the MOCVD. High cleaning performance that maintains condition of reactor components results in constant perfect growth conditions.

UR26K-CCD Specifications

Wafer size	8" x 6 or 6" x 10
Reactor type	Rotation/revolution
Wafer face	Face up
Rotation/revolution mechanism	Mechanical/mechanical (for stable revolution/rotation motion)
Gas flow	Three laminar flow horizontals
Growth pressure	Low to atmospheric pressure High flow velocity narrow channel
Heating system	6 zone resistance heaters

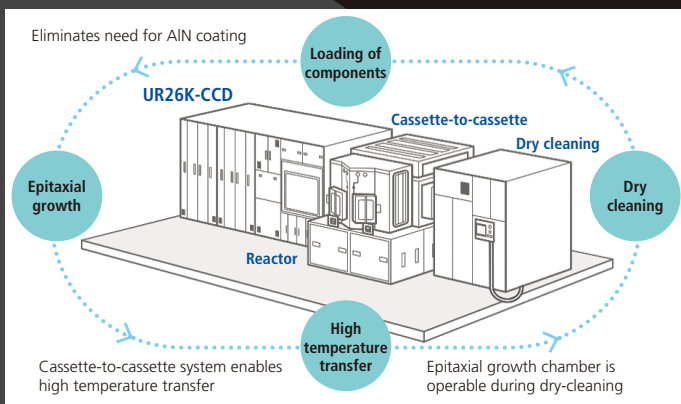
Before and after cleaning



Before cleaning

After cleaning

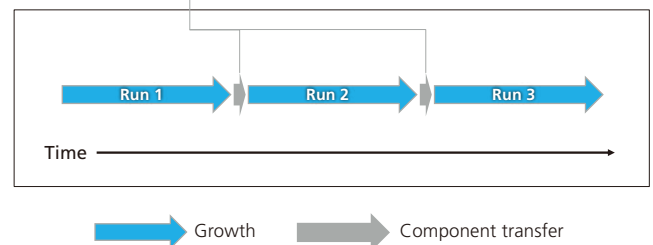
Concept of UR26K-CCD



Reactor operation

Continuous epi-growth with a maximum of only 15 minutes inter-process transition

Reactor uptime of up to 90%



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